

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI FMB175** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CB0}	65 V
V_{CEO}	36 V
V_{CES}	65 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.7 °C/W

PACKAGE STYLE .500 6L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B	.045 / 1.14	
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H	.125 / 3.18	
I	.725 / 18.42	
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M	.285 / 7.24	
N	.120 / 3.05	.135 / 3.43

ORDER CODE: ASI10589

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 100 mA	65			V
BV_{CES}	I _C = 100 mA	65			V
BV_{CEO}	I _C = 100 mA	35			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _{CE} = 28 V			15	mA
h_{FE}	V _{CE} = 5.0 V I _C = 5.0 A	20		200	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			200	pF
P_G η_C	V _{CC} = 28 V P _{OUT} = 175 W f = 108 MHz	10	65		dB %